RF POWER MOSFET

DESCRIPTION:

The **ASI MRF185** is a Silicon N-channel enhancement mode lateral MOSFET.

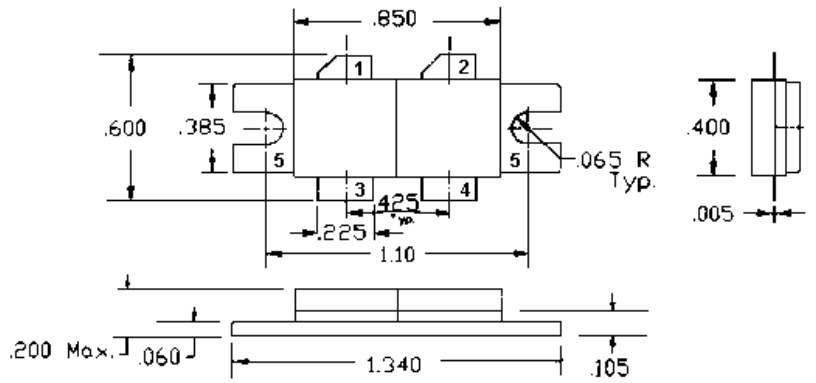
FEATURES:

- High Gain, Rigged Device
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

V_{DS}	65 V
V_{GS}	±15 V
P_{DISS}	250 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.7 °C/W

PACKAGE STYLE .385X.850 4LFG



1 & 2 = DRAIN 3 & 4 = GATE
5 = SOURCE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_D = 1.0 µA			65			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				1.0	µA
I_{GSS}	V_{DS} = 0 V	V_{GS} = 20 V				1.0	µA
$\Delta V_{GS(Q)}$	I_D = 300 mA	V_{DS} = 26 V			0.15	0.3	V
$V_{DS(on)}$	I_D = 3.0 A	V_{GS} = 3 V			0.75		V
g_{fs}	I_D = 3.0 A	V_{DS} = 10 V		1.6			S
C_{oss} C_{rss}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		38 4.6		pF
G_{PS}	V_{DS} = 28 V	P_{out} = 85 W	f = 960 MHz	11	14		dB
η_D				45	53		%

Specifications are subject to change without notice.